L Number	Hits	Search Text	DB	Time stamp
1	178	have has having	USPAT	2003/09/23 11:28
2	1431	silicon adj sapphire	USPAT	2003/09/23 11:28
3	14	(silicon adj sapphire) with (advantage benefit better)	USPAT	2003/09/23 13:14
4	18685	gallium adj arsenide	USPAT	2003/09/23 11:32
5	308	(gallium adj arsenide) with (advantage benefit better)	USPAT	2003/09/23 12:10
6	28708	germanium	USPAT	2003/09/23 12:10
7	442	germanium with (advantage benefit better)	USPAT	2003/09/23 12:17
8	1	("6143072").PN.	USPAT;	2003/09/23 12:17
-	·	(• • • • • • • • • • • • • • • • • • •	US-PGPUB	2000/00/20 12:17
9	1	("5994985").PN.	USPAT:	2003/09/23 12:23
-	Ť	(333)	US-PGPUB	2000/00/20 12:20
10	1	("4906594").PN.	USPAT:	2003/09/23 13:14
	·		US-PGPUB	2000/00/20 10:14
11	8067	thermal adj oxide	USPAT;	2003/09/23 16:26
1		and any oxido	US-PGPUB	2000/00/20 10:20
12	107	(thermal adj oxide) with (advantage benefit better)	USPAT	2003/09/23 14:16
13	1898	(thermal adj oxide) with gate	USPAT;	2003/09/23 13:31
		(mornial day oxido) with guite	US-PGPUB	2003/03/23 13.31
14	0	((thermal adj oxide) with gate) same for	USPAT:	2003/09/23 13:30
, ,		((thermal adjoxide) with gate) same for	US-PGPUB	2003/03/23 13.30
15	1078	((thermal adj oxide) with gate) same substrate	USPAT:	2003/09/23 13:31
.0	1070	((thermal adjoxide) with gate) same substrate	US-PGPUB	2003/09/23 13.31
16	827	((thermal adj oxide) with gate) same substrate	USPAT	2003/09/23 13:31
17	0	(("6143072").PN.) same transistor	USPAT	2003/09/23 13:31
18	232	(((thermal adj oxide) with gate) same substrate) same	USPAT	2003/09/23 13:32
.0	202	transistor	USFAI	2003/09/23 13.32
19	269	(thermal adj oxide) with (advantage benefit better improv\$3)	USPAT	2003/09/23 13:46
20	162	((thermal adj oxide) with (advantage benefit better improv\$3)	USPAT	2003/09/23 13:46
	102	not ((thermal adj oxide) with (advantage benefit better))	USFAI	2003/09/23 13.40
21	0	gate adj oxide same thermal adj oxxide	USPAT	2003/09/23 14:16
22	897	gate adj oxide same thermal adj oxide	USPAT	2003/09/23 14:10
23	1	("20020030539").PN.	USPAT:	2003/09/23 14:46
-0	•	(2002000000 j.i 14.	US-PGPUB	2003/09/23 14.46
24	368	thermal adj oxide with (better higher improv\$3)	USPAT	2003/09/23 14:48
25	39	thermal adj oxide with (better higher improv\$3)	USPAT	2003/09/23 14:48
26	664	silicon adj (oxide near dioxide)	USPAT	2003/09/23 16:20
27	0	(silicon adj (oxide near dioxide)) with (benefit better	USPAT	2003/09/23 16:21
ļ - '		advantage improv\$3)	USFAI	2003/08/23 10.21
28	1	("4868619").PN.	USPAT:	2003/09/23 16:24
	•	(1000010) 14.	US-PGPUB	2003/03/23 10.24
29	409	11.ab.	USPAT;	2003/09/23 16:26
	.50		US-PGPUB	2003/09/23 10.20
30	307	11.ab. and (transistor FET MOSFET CMOS)	USPAT;	2003/09/23 16:27
	557	11.db. did (idilalator ET MOOI ET OMOO)	US-PGPUB	2003/09/23 10:27
31	13	11.ti.	USPAT;	2002/00/22 47:42
•	13	11.41.		2003/09/23 17:13
32	1	("6143072").PN.	US-PGPUB	2002/00/02 47:40
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